

ABSTRACT

There is provided a method for forming a pattern of metal oxide capable of selectively etching an etching
5 object containing metal oxide relative to a non-etching object and forming a pattern of the metal oxide having the shape along the shape of a pattern of the non-etching object serving as a template for forming the pattern of the metal oxide. Metal oxide containing oxide of at
10 least one of tin and indium is etched using an etching gas to form the pattern of the metal oxide. An etching gas containing halon is brought into contact with a member to be etched in the presence of plasma, and etching is performed while a bias power is being applied
15 to a lower electrode (2) supporting the member to be etched to selectively etch a metal oxide layer (22) relative to a silicon substrate (24), a template layer (21), and an underlying layer (23), and the predetermined pattern of the template layer (21) is transferred to the
20 metal oxide layer (22).

Fig. 2